

FDN302P

P-Channel 2.5V Specified PowerTrench® MOSFET -20V, -2.4A, 55mΩ

Product Overview

For complete documentation, see the data sheet.

This P-Channel 2.5V specified MOSFET uses a rugged gate version of an advanced PowerTrench process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V – 12V).

Features

- -20 A, -2.4 V.
- RDS(ON)= 0.055 @ VGS = -4.5 V
- RDS(ON) = 0.080 @ VGS = -2.5 V
- Fast switching speed
- High performance trench technology for extremely low RDS(ON)
- SuperSOT™ -3 provides low RDS(ON) and 30% higher power handling capability than SOT23 in the same footprint

Applications

- This product is general usage and suitable for many different applications.
- Power Management
- Load Switch
- Battery Protection

Part Electrical Specifications

Product	Status	Compliance	Channel Polarity	Configuration	V <sub>DS</sub> (BR) Min (V)	V <sub>GS</sub> Max (V)	V <sub>GS</sub> (th) Max (V)	I <sub>D</sub> Max (A)	P <sub>D</sub> Max (W)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 2.5 V (mΩ)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 4.5 V (mΩ)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 10 V (mΩ)	Q <sub>g</sub> Typ @ V <sub>GS</sub> = 4.5 V (nC)	Q <sub>g</sub> Typ @ V <sub>GS</sub> = 10 V (nC)	C <sub>iss</sub> Typ (pF)	Package Type
FDN302P	Active		P-Channel	Single	-20.0	12.0	-1.5	-2.4	0.5	80.0	55.0	-	12.0	9.0	882.0	SOT-23-3